IIN THE CLAIMS:

Please amend the claims to read as follows:

1 (Currently Amended): An organic EL cell for preventing moisture that deteriorates the light-emitting characteristics of the organic EL cell, comprising:

a substrate;

a laminate structure formed on the substrate, wherein the laminate structure includes at least an anode, an organic light emitting layer, and a cathode;

a first sealing film of an inorganic material formed on the cathode of the laminate structure;

a second sealing film of an organic material formed on the first sealing film; and

a third sealing film of an inorganic material formed on the second sealing film.

2 (Original): The organic EL cell of claim 1, wherein the first sealing film is an inorganic passivation film and the second sealing film is a resin film.

3 (Previously Presented): The organic EL cell of claim 1, wherein the third sealing film is an inorganic passivation film.

4 (Original): The organic EL cell of claim 3, wherein the first sealing film and the third sealing film are selected from a group consisting of silicon nitride, SiO_2, Al_2O_3, and diamond-like carbon (DLC).

5 (Cancelled)

6 (Cancelled)

7 (Cancelled)

8 (Cancelled)

9 (Previously Presented): The organic EL cell of claim 4, wherein the first sealing film and the third sealing film are formed by vapor deposition.

10 (Currently Amended): A method for producing an organic EL cell for preventing moisture that deteriorates the light-emitting characteristics of the organic EL cell and that includes a substrate and a laminate structure formed on the substrate, wherein the laminate structure includes at least an anode, an organic light emitting layer, and a cathode, comprising the steps of forming a first sealing film of an inorganic material on the cathode of the laminate structure, forming a second sealing film of an organic material on the first sealing film, and forming a third sealing film of an inorganic material on the second sealing film.

11 (Original): The method of claim 10, wherein the first sealing film is an inorganic passivation film and the second sealing film is a resin film.

12 (Previously Presented): The method of claim 11, wherein the third sealing film is an inorganic passivation film.

13 (Original): The method of claim 12, wherein the first sealing film and the third sealing film are selected from a group consisting of silicon nitride, SiO_2, Al_2O_3, and diamond-like carbon (DLC).

14 (Cancelled)

15 (Cancelled)

16 (Cancelled)

17 (Cancelled)

18 (Previously Presented): The method of claim 13, wherein the first sealing film and the third sealing film are formed by vapor deposition.

19 (Cancelled)

20 (Cancelled)

21 (Original): The method of 13, wherein the inorganic passivation film is that of silicon nitride formed by a plasma CVD.

22 (Original): The method of claim 21, wherein the silicon nitride is formed by the plasma CVD from a raw material gas composed only of silane and nitrogen.

23 (Previously Presented): The organic EL cell of claim 1, wherein the second sealing film is formed contacting the first sealing film, and wherein the third sealing film is formed contacting the second sealing film.

24 (Previously Presented): The organic EL cell of claim 23, wherein the first sealing film is formed contacting the entire surface of the laminate structure to passivate the cathode.

25 (New): The organic EL cell of claim 1, wherein the first sealing film is formed directly on the cathode of the laminate structure.

26 (New): The organic EL cell of claim 4, wherein the first sealing film is formed directly on the cathode of the laminate structure.

27 (New): The method of claim 10, wherein the first sealing film is formed directly on the cathode of the laminate structure.

28 (New): The method of claim 13, wherein the first sealing film is formed directly on the cathode of the laminate structure.